



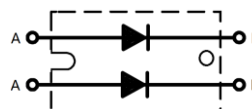
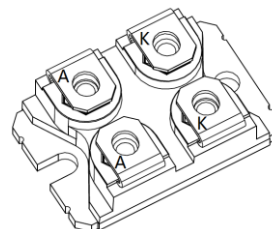
FP120F60ADNS1

主要参数 MAIN CHARACTERISTICS

$I_F(AV)$	60*2 A
V_{RRM}	600 V
$V_F(\text{typ})$	1.8 V
$t_{rr}(\text{typ})$	48ns

封装 Package

SOT-227



用途

- UPS
- PFC
- 逆变焊机
- 光伏逆变

APPLICATIONS

- UPS
- PFC
- Inversion Welder
- Solar inverter

产品特性

- 平面钝化芯片
- 低功耗，高效率
- 短恢复时间
- 软恢复特性

FEATURES

- Planar passivated chips
- Low power loss, high efficiency
- Very short recovery time
- Soft Recovery Characteristics

订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package	包装 Packaging	器件重量 Device Weight
FP120F60ADNS1-NS1-BR	FP120F60ADNS1	SOT-227	条管	165g



绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最大反向重复峰值电压 Repetitive peak reverse voltage	V _{RRM}	600	V
正向平均整流电流 Average forward Current T _c =100°C	I _{F(AV)}	per module 120	A
		per diode 60	
峰值单脉冲浪涌电流 Peak one Cycle Surge Forward Current(Non-Repetitive) t=8.3ms	I _{FSM}	480	A
结温 Junction Temperature	T _j	-50~+175	°C
储存温度 Storage temperature range	T _{STG}	-50~+175	°C

电特性 ELECTRICAL CHARACTERISTICS (Tc=25°C PER DIODE)

项 目 Parameter	测试条件 Tests conditions		最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单位 Unit
V _R	I _R = 50μA		600	-	-	V
I _R	T _j = 25°C	V _R = V _{RRM}	-	-	10	μA
	T _j = 125°C		-	-	800	μA
V _F	T _j = 25°C	I _F = 60A	-	1.8	2.2	V
	T _j = 125°C		-	1.5	2.0	V
trr	I _F = 0.5A, I _R = 1A, I _{RR} = 0.25A		-	48	55	ns
trr	I _F = 1A, V _R = 30V, di _F /dt = -100A/μs		-	-	45	ns
trr	I _F = 60A, V _R = 200V, di _F /dt = -200A/μs T _c = 25°C		-	27	-	ns
Q _{rr}			-	33	-	nc
I _{RRM}			-	1.5	-	A
trr	I _F = 60A, V _R = 200V, di _F /dt = -200A/μs T _c = 125°C		-	91	-	ns
Q _{rr}			-	173	-	nc
I _{RRM}			-	3.8	-	A

热特性 THERMAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	最大值 Value(max)	单 位 Unit
结到管壳的热阻 Thermal resistance from junction to case	R _{th(j-c)}	per diode 0.6	°C/W
		per module 0.35	





特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Fig.1 TYPICAL FORWARD CHARACTERISTICS

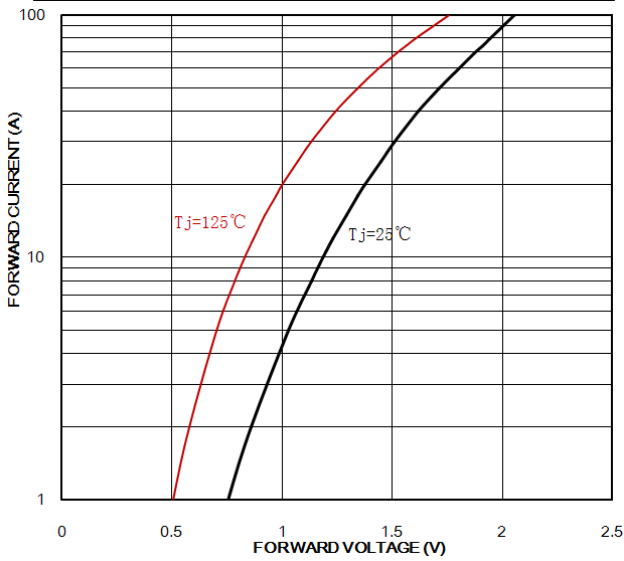


Fig.2 TYPICAL REVERSE CHARACTERISTICS

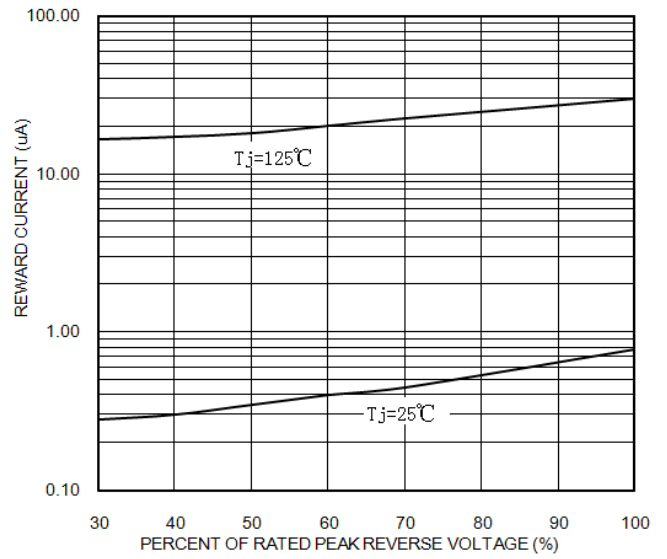


Fig.3 TYPICAL JUNCTION CAPACITANCE

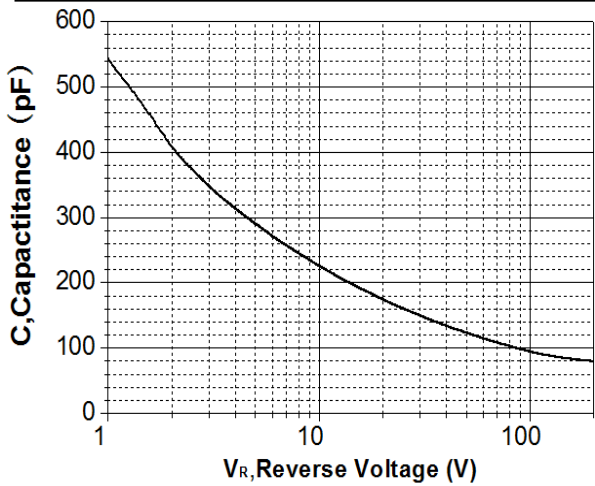


Fig.4 Reverse recovery time versus di/dt

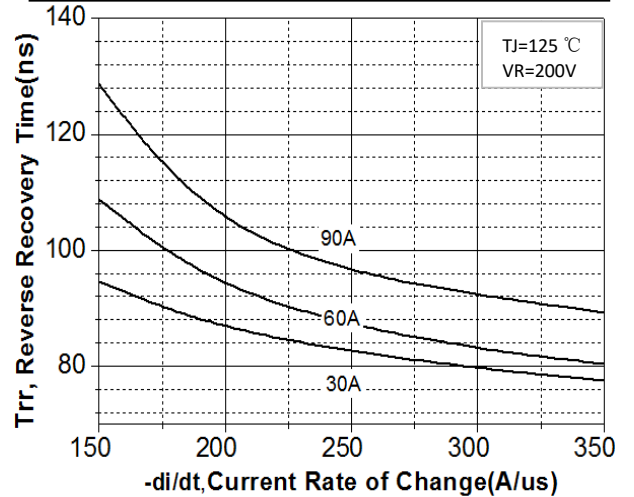


Fig.5 Reverse recovery charges versus di/dt

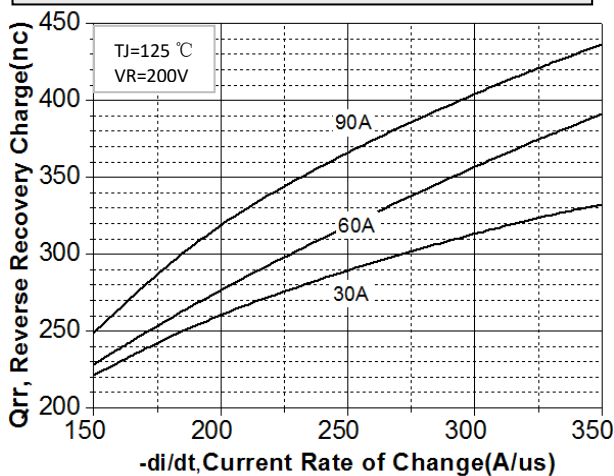
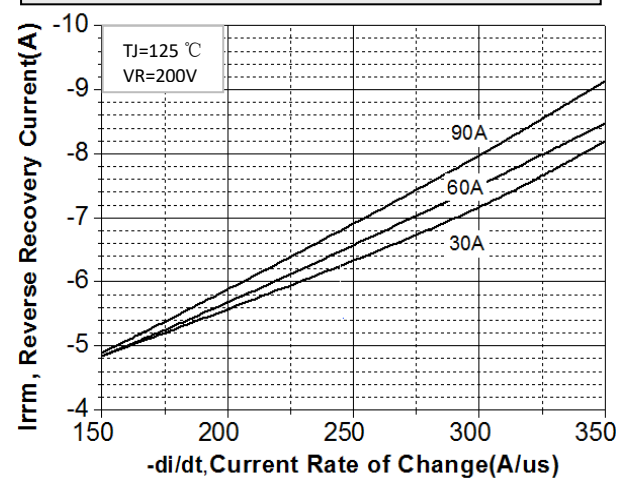


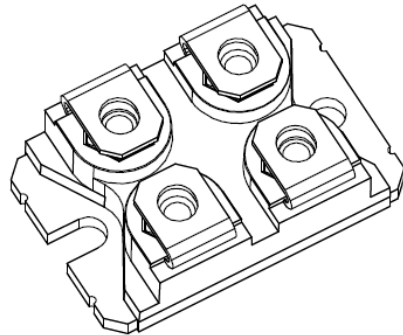
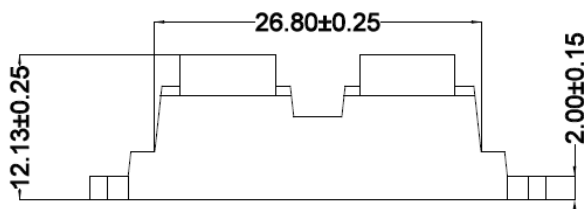
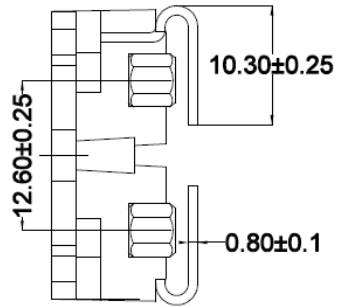
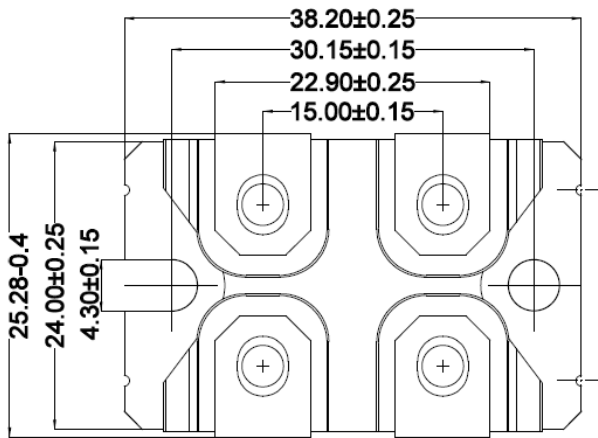
Fig.6 Peak reverse recovery current versus di/dt





SOT-227

单位 Unit : mm





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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知。

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
4. Jilin Sino-microelectronics co., Ltd reserves the right to make changes in this. specification sheet and is subject to change without prior notice.

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